



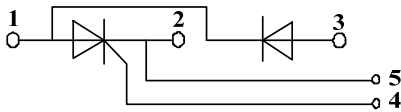
Thyristor/Diode Modules

V_{RRM} / V_{DRM} 800 to 1800V
 I_{FAV} / I_{TAV} 110A

Applications

- Power Converters
- Lighting Control
- DC Motor Control and Drives
- Heat and temperature control

Circuit



Features

- International standard package
- High Surge Capability
- Glass passivated chip
- Simple Mounting
- Heat transfer through aluminum oxide DBCceramic isolated metal baseplate
- UL recognized applied for file no. E230084

Module Type

TYPE	V_{RRM}/V_{DRM}	V_{RSM}
MT110CB08T1	800V	900V
MT110CB12T1	1200V	1300V
MT110CB16T1	1600V	1700V
MT110CB18T1	1800V	1900V

◆Diode

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_D	Output Current(D.C.)	$T_c=85^{\circ}\text{C}$	110	A
I_{FSM}	Surge forward current	$t=10\text{ms } T_{vj}=45^{\circ}\text{C}$	2250	A
i^2t	Circuit Fusing Consideration		25000	A^2s
V_{isol}	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
M_t	Mounting Torque	To terminals(M5)	$3\pm 15\%$	Nm
M_s		To heatsink(M6)	$5\pm 15\%$	Nm
Weight	Module (Approximately)		100	g

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.14	$^{\circ}\text{C}/\text{W}$
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink	0.10	$^{\circ}\text{C}/\text{W}$

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V_{FM}	Forward Voltage Drop, max.	$T=25^{\circ}\text{C } I_F=300\text{A}$			1.30	V
I_{RRM}	Repetitive Peak Reverse Current, max.	$T_{vj}=25^{\circ}\text{C } V_{RD}=V_{RRM}$ $T_{vj}=125^{\circ}\text{C } V_{RD}=V_{RRM}$		≤ 0.5 ≤ 6		mA mA



◆Thyristor

Maximum Ratings

Symbol	Item	Conditions	Values	Units
I_{TAV}	Average On-State Current	Sine 180°; $T_c=85^{\circ}\text{C}$	110	A
I_{TSM}	Surge On-State Current	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$, sine $T_{VJ}=125^{\circ}\text{C}$ $t=10\text{ms}$, sine	2250 1900	A
i^2t	Circuit Fusing Consideration	$T_{VJ}=45^{\circ}\text{C}$ $t=10\text{ms}$, sine $T_{VJ}=125^{\circ}\text{C}$ $t=10\text{ms}$, sine	25000 18000	A ² s
V_{isol}	Isolation Breakdown Voltage(R.M.S)	a.c.50HZ;r.m.s.;1min	3000	V
T_{vj}	Operating Junction Temperature		-40 to +130	$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40 to +125	$^{\circ}\text{C}$
M_t	Mounting Torque	To terminals(M5)	$3 \pm 15\%$	Nm
M_s		To heatsink(M6)	$5 \pm 15\%$	Nm
di/dt	Critical Rate of Rise of On-State Current	$T_{VJ}=T_{VJM}$, $2/3V_{DRM}$, $I_G=500\text{mA}$ $T_r<0.5\mu\text{s}$, $t_p>6\mu\text{s}$	150	A/ μs
dv/dt	Critical Rate of Rise of Off-State Voltage, min.	$T_J=T_{VJM}$, $2/3V_{DRM}$ linear voltage rise	1000	V/ μs
a	Maximum allowable acceleration		50	m/s^2

Thermal Characteristics

Symbol	Item	Conditions	Values	Units
$R_{th(j-c)}$	Thermal Impedance, max.	Junction to Case	0.28	$^{\circ}\text{C/W}$
$R_{th(c-s)}$	Thermal Impedance, max.	Case to Heatsink	0.20	$^{\circ}\text{C/W}$

Electrical Characteristics

Symbol	Item	Conditions	Values			Units
			Min.	Typ.	Max.	
V_{TM}	Peak On-State Voltage, max.	$T=25^{\circ}\text{C}$ $I_T=300\text{A}$			1.65	V
I_{RRM}/I_{DRM}	Repetitive Peak Reverse Current, max. / Repetitive Peak Off-State Current, max.	$T_{VJ}=T_{VJM}$, $V_R=V_{RRM}$, $V_D=V_{DRM}$			20	mA
V_{TO}	On state threshold voltage	For power-loss calculations only ($T_{VJ}=125^{\circ}\text{C}$)			0.9	V
r_T	Value of on-state slope resistance. max	$T_{VJ}=T_{VJM}$			2	$\text{m}\Omega$
V_{GT}	Gate Trigger Voltage, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$			3	V
I_{GT}	Gate Trigger Current, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$			150	mA
V_{GD}	Non-triggering gate voltage, max.	$T_{VJ}=125^{\circ}\text{C}$, $V_D=2/3V_{DRM}$			0.25	V
I_{GD}	Non-triggering gate current, max.	$T_{VJ}=125^{\circ}\text{C}$, $V_D=2/3V_{DRM}$			6	mA
I_L	Latching current, max.	$T_{VJ}=25^{\circ}\text{C}$, $R_G=33\Omega$		300	600	mA
I_H	Holding current, max.	$T_{VJ}=25^{\circ}\text{C}$, $V_D=6\text{V}$		150	250	mA
t_{gd}	Gate controlled delay time	$T_{VJ}=25^{\circ}\text{C}$, $I_G=1\text{A}$, $di/dt=1\text{A}/\mu\text{s}$	1			μs
t_q	Circuit commutated turn-off time	$T_{VJ}=T_{VJM}$	100			μs



Performance Curves

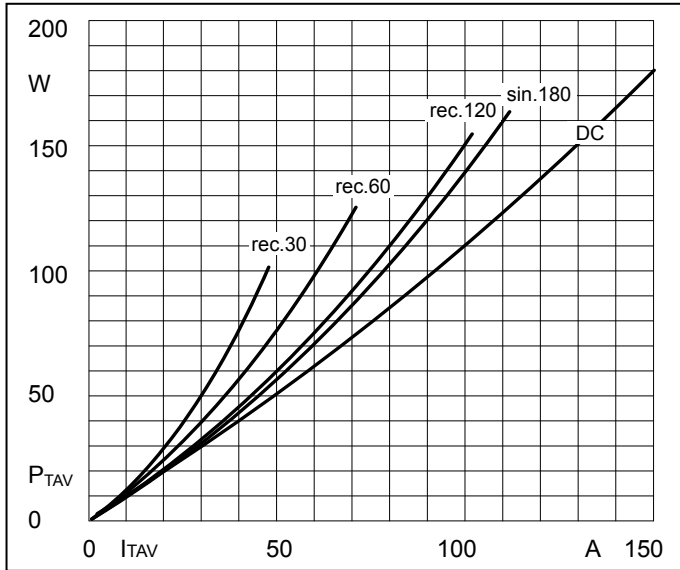


Fig1. Power dissipation

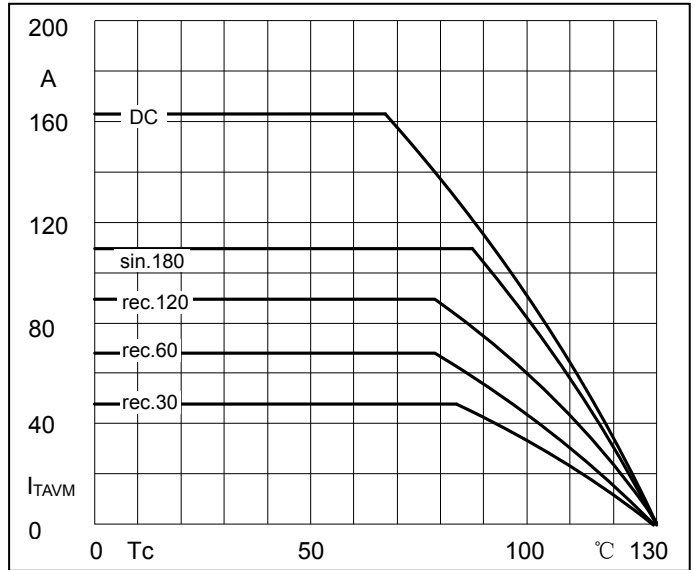


Fig2. Forward Current Derating Curve

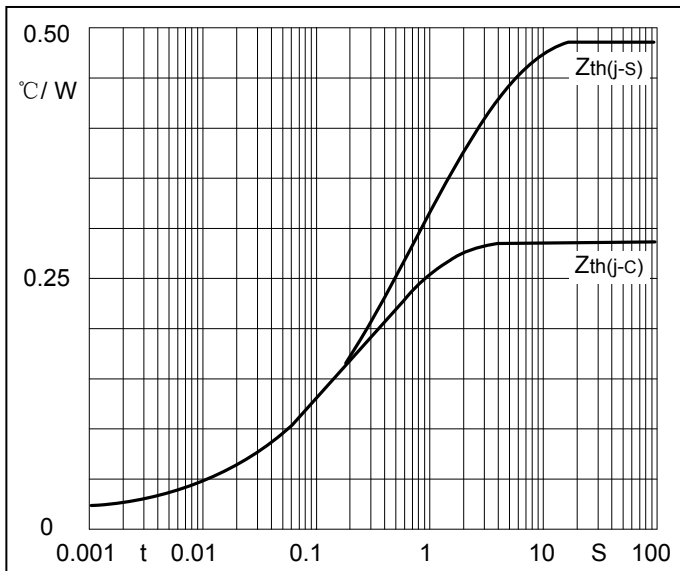


Fig3. Transient thermal impedance

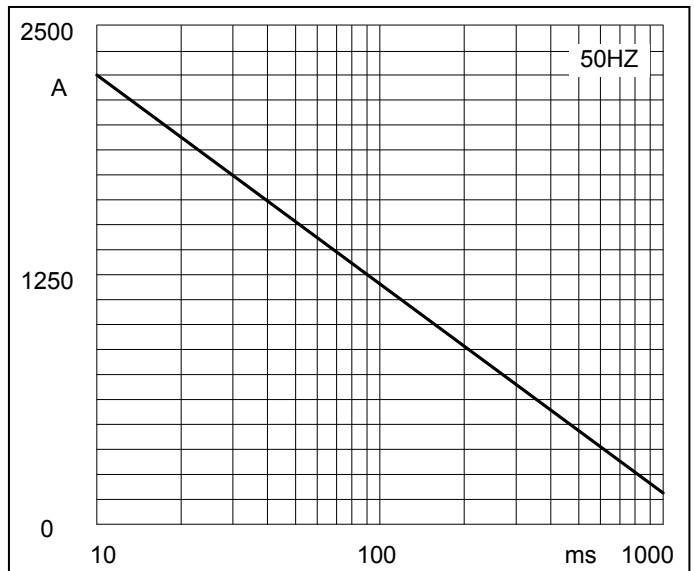


Fig4. Max Non-Repetitive Forward Surge Current

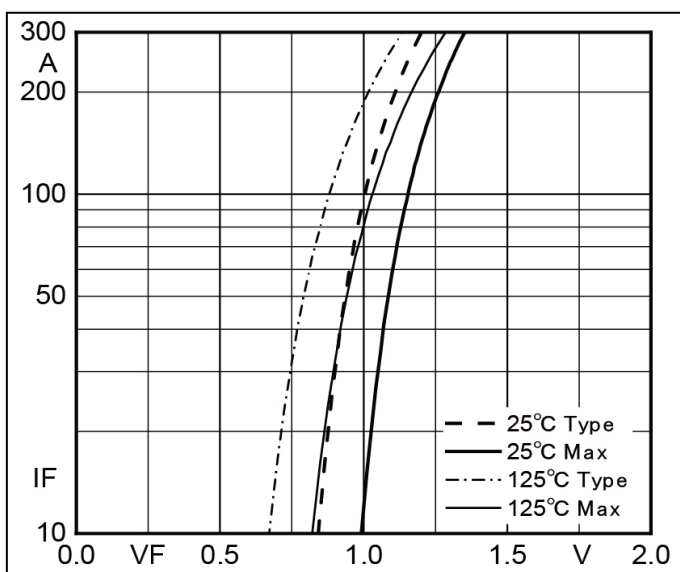


Fig5. Forward Characteristics

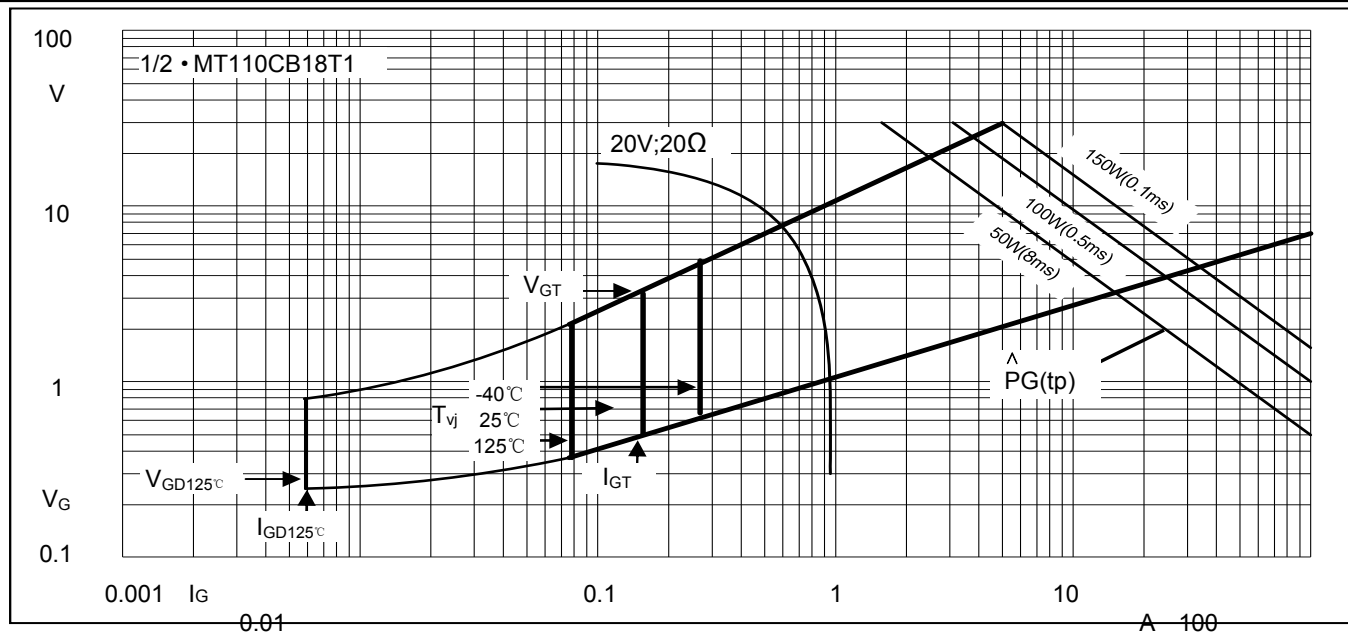
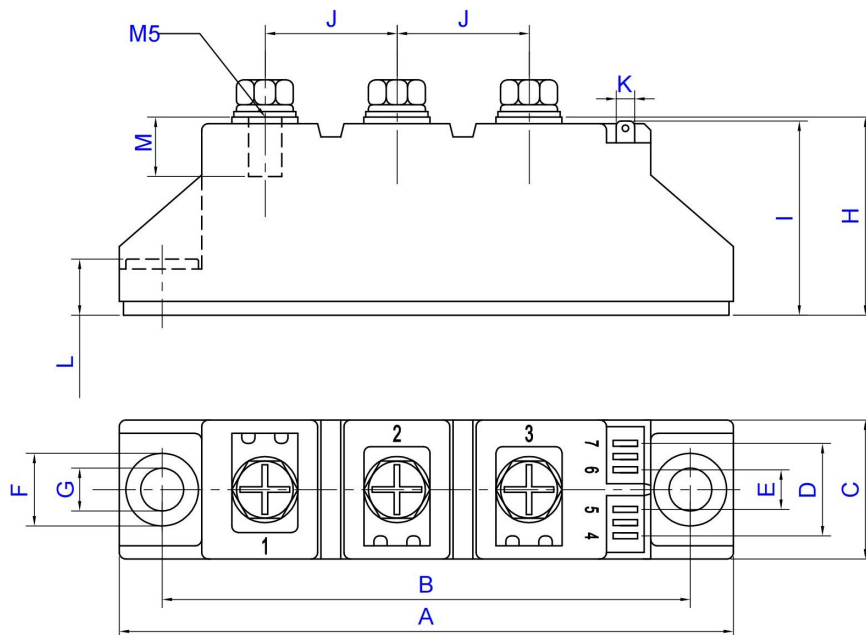


Fig6. Gate trigger Characteristics

Package Outline Information

CASE: T1



DIM	Min (mm)	Max (mm)	Note
A	92.5	93.5	
B	79.5	80.5	
C	20.5	21.5	
D	13.5	14.5	
E	5.5	6.5	
F	10.5	11.5	
G	6.2	6.8	Ø
H	29.5	30.5	
I	28.5	29.5	
J	19.5	20.5	
K	2.3	3.5	
L	8.2	8.8	
M	8.5	9.5	



Packing Standard

Item	Length: A (mm)	Width: B (mm)	Height: C (mm)	Quantity (PCS)
Inner Box	276	258	48	10
Outer Carton	545	295	240	100

Disclaimer

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